

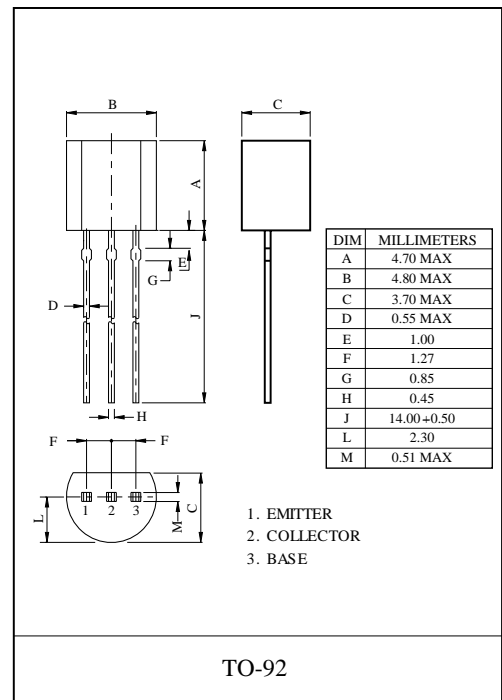
General Purpose Transistor PNP Silicon

FEATURE

- High DC Current Gain
- Complementary to KTC3203

MAXIMUM RATINGS ($T_a=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CB0}	Collector-Base Voltage	-35	V
V_{CE0}	Collector-Emitter Voltage	-30	V
V_{EB0}	Emitter-Base Voltage	-5	V
I_C	Collector Current	-0.8	A
P_C	Collector Power Dissipation	0.625	W
$R_{\theta JA}$	Thermal Resistance From Junction To Ambient	200	$^\circ\text{C/W}$
T_j	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature	-55~+150	$^\circ\text{C}$



ELECTRICAL CHARACTERISTICS ($T_{amb}=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -0.1\text{mA}, I_E = 0$	-35			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -10\text{mA}, I_B = 0$	-30			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -0.1\text{mA}, I_C = 0$	-5			V
Collector cut-off current	I_{CBO}	$V_{CB} = -35\text{V}, I_E = 0$			-0.1	μA
Collector cut-off current	I_{CEO}	$V_{CE} = -25\text{V}, I_B = 0$			-0.2	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = -5\text{V}, I_C = 0$			-0.1	μA
DC current gain	$h_{FE(1)}$	$V_{CE} = -1\text{V}, I_C = -100\text{mA}$	100		320	
	$h_{FE(2)}$	$V_{CE} = -1\text{V}, I_C = -700\text{mA}$	35			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -500\text{mA}, I_B = -20\text{mA}$			-0.7	V
Base-emitter voltage	V_{BE}	$V_{CE} = -1\text{V}, I_C = -10\text{mA}$			-0.8	V
Transition frequency	f_T	$V_{CE} = -5\text{V}, I_C = -10\text{mA}$		120		MHz
Collector Output Capacitance	C_{ob}	$V_{CB} = -10\text{V}, I_E = 0, f = 1\text{MHz}$		19		pF

CLASSIFICATION OF $h_{FE(1)}$

RANK	O	Y
RANGE	100-200	160-320

Typical Characteristics

